

**Silicon PNP Power Transistors****2SA1280****DESCRIPTION**

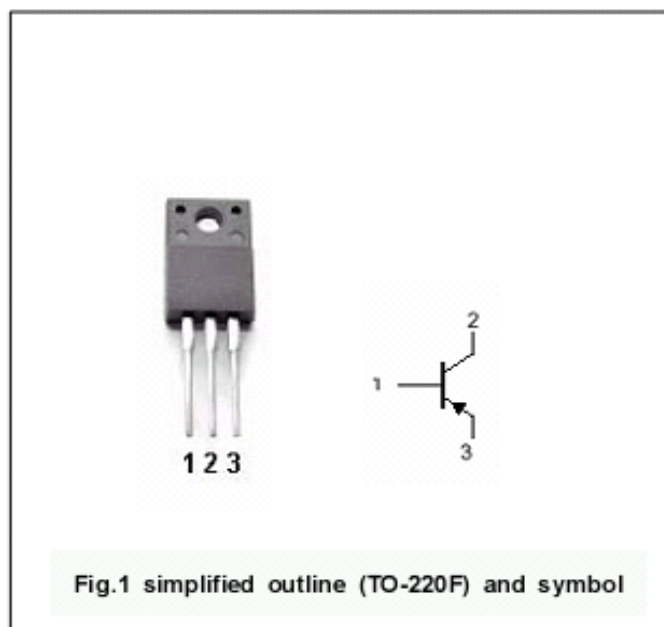
- With TO-220F package
- High breakdown voltage
- High power dissipation

APPLICATIONS

- For use in low frequency power amplifier
Color TV vertical deflection output

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

**Absolute maximum ratings (Ta=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-150	V
V_{CEO}	Collector-emitter voltage	Open base	-150	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-1.5	A
P_C	Collector dissipation	$T_C=25^{\circ}\text{C}$	25	W
T_J	Junction temperature		150	$^{\circ}\text{C}$
T_{stg}	Storage temperature		-55~150	$^{\circ}\text{C}$

**Silicon PNP Power Transistors****2SA1280****CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA ; I _B =0	-150			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-500mA; I _B =-50mA			-3.0	V
V _{BE}	Base-emitter on voltage	I _C =-50mA ; V _{CE} =-4V			-1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-120V; I _E =0			-1	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =-6V; I _C =0			-1	μ A
h _{FE-1}	DC current gain	I _C =-50mA ; V _{CE} =-4V	60		200	
h _{FE-2}	DC current gain	I _C =-500mA ; V _{CE} =-10V	60			
f _T	Transition frequency	I _C =-500mA ; V _{CE} =-10V	4			MHz
C _{OB}	Output capacitance	I _E =0 ; V _{CB} =-100V; f=1MHz		30		pF



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PACKAGE OUTLINE

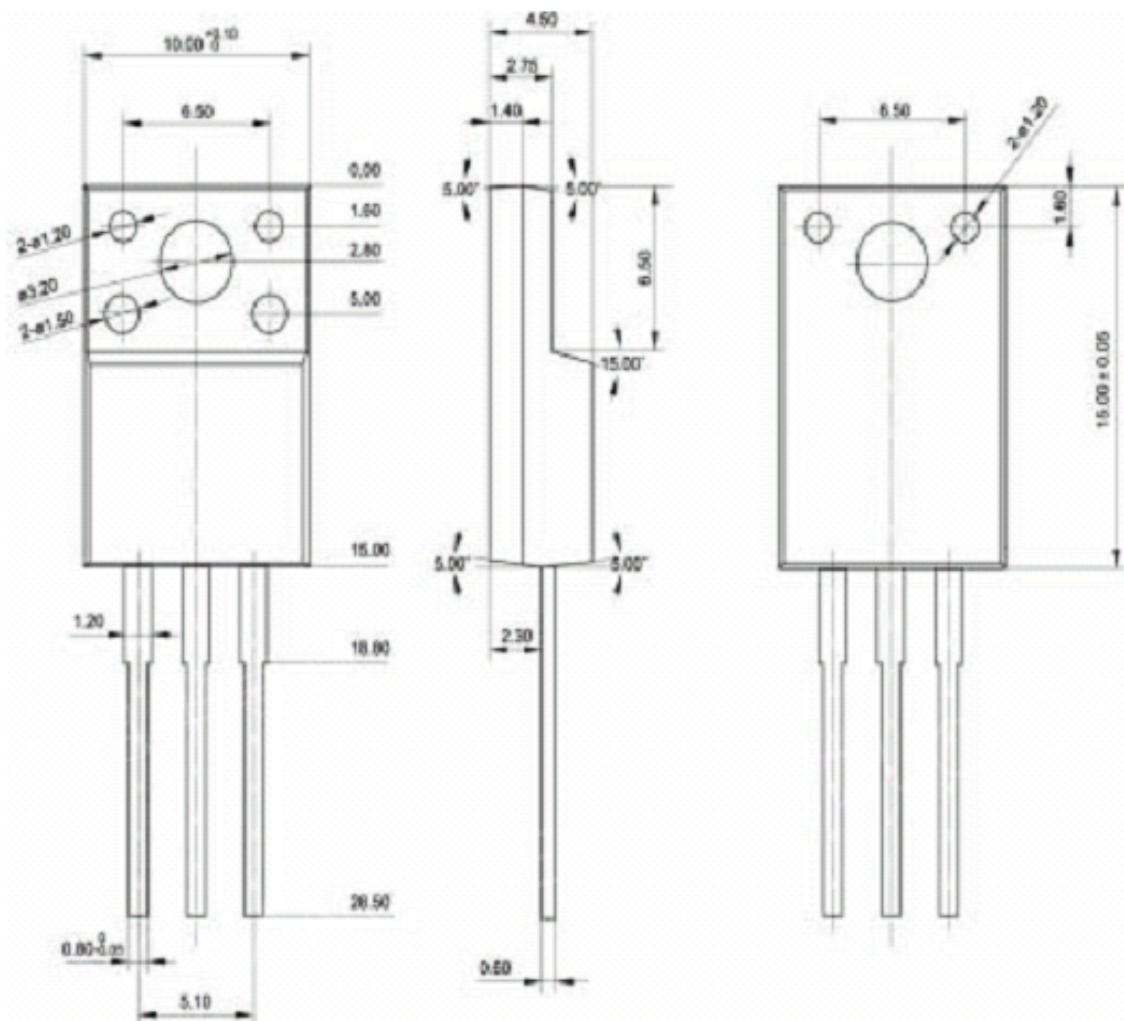


Fig.2 Outline dimensions